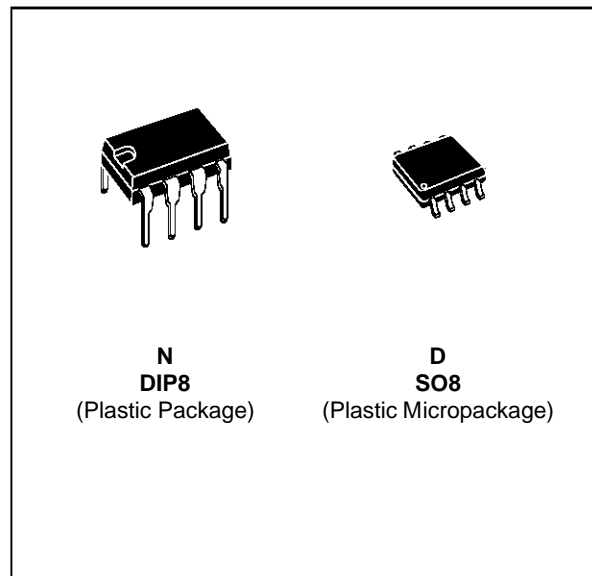


INPUT/OUTPUT RAIL TO RAIL DUAL CMOS OPERATIONAL AMPLIFIER

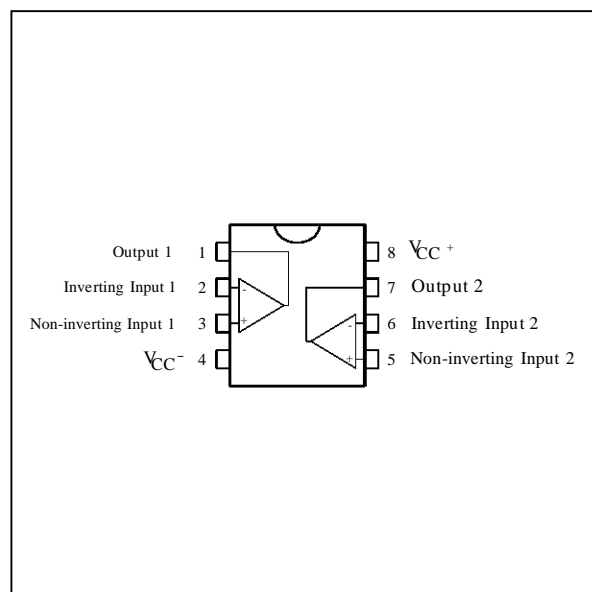
- **RAIL TO RAIL** INPUT AND OUTPUT VOLTAGE RANGES
- SINGLE (OR DUAL) SUPPLY OPERATION FROM **2.7V TO 16V** ($\pm 1.35V$ to $\pm 8V$)
- EXTREMELY LOW INPUT BIAS CURRENT : **1pA TYP**
- LOW INPUT OFFSET VOLTAGE : **2mV max.**
- SPECIFIED FOR **600Ω** AND **100Ω** LOADS
- LOW SUPPLY CURRENT : 400μA/Ampli
- SPEED : 1.4MHz - 1.3V/μs
- ESD TOLERANCE : 3KV
- LATCH-UP IMMUNITY
- **SPICE MACROMODEL** INCLUDED IN THIS SPECIFICATION



ORDER CODES

Part Number	Temperature Range	Package	
		N	D
TS912I/AI/BI	-40, +125°C	•	•

PIN CONNECTIONS (top view)



DESCRIPTION

The TS912 is a RAIL TO RAIL dual CMOS operational amplifier designed to operate with single or dual supply voltage.

The input voltage range V_{icm} includes the two supply rails V_{CC}^+ and V_{CC}^- .

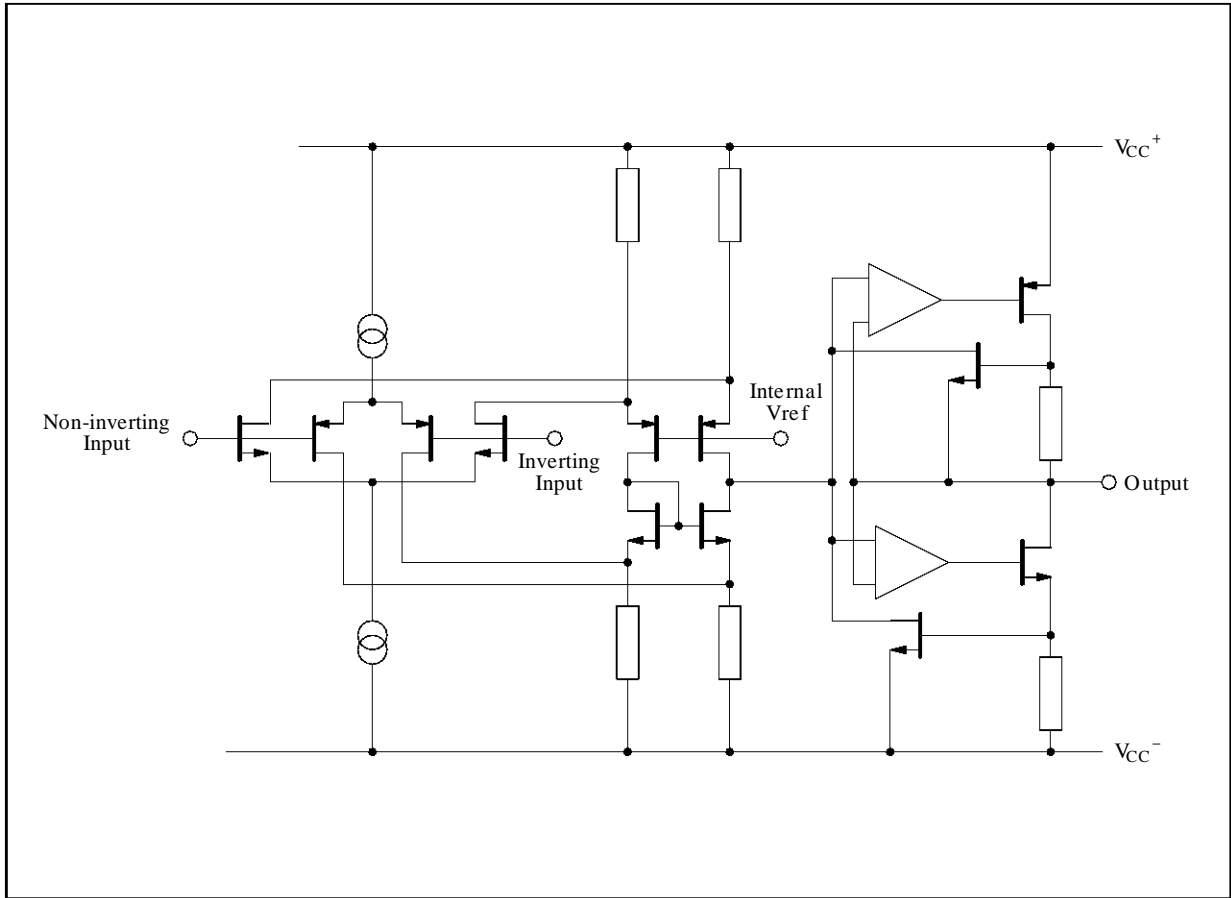
The output reaches :

- $V_{CC}^- + 50mV$ $V_{CC}^+ - 50mV$ with $R_L = 10k\Omega$
- $V_{CC}^- + 650mV$ $V_{CC}^+ - 650mV$ with $R_L = 600\Omega$

This product offers a broad supply voltage operating range from 2.7V to 16V, a supply current of only 400μA/amp ($V_{CC} = 10V$) and a high output current capability fixed by an internal limitation circuit :

$$I_{source} = 65mA - I_{sink} = 75mA$$

SCHEMATIC DIAGRAM (1/2 TS912)



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage - (note 1)	18	V
V_{id}	Differential Input Voltage - (note 2)	± 18	V
V_i	Input Voltage - (note 3)	-0.3 to 18	V
I_{in}	Current on Inputs	± 50	mA
I_o	Current on Outputs	± 130	mA
T_{oper}	Operating Free Air Temperature Range	-40 to +125	$^{\circ}C$
T_{stg}	Storage Temperature	-65 to +150	$^{\circ}C$

Notes : 1. All voltage values, except differential voltage are with respect to network ground terminal.
 2. Differential voltages are the non-inverting input terminal with respect to the inverting input terminal.
 3. The magnitude of input and output voltages must never exceed $V_{CC}^{+} + 0.3V$.

OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	2.7 to 16	V
V_{icm}	Common Mode Input Voltage Range	$V_{CC}^{-} - 0.2$ to $V_{CC}^{+} + 0.2$	V

ELECTRICAL CHARACTERISTICS

$V_{CC^+} = 10V$, $V_{CC^-} = 0V$, R_L, C_L connected to $V_{CC}/2$, $T_{amb} = 25^{\circ}C$ (unless otherwise specified)

Symbol	Parameter	TS912I/AI/BI			Unit
		Min.	Typ.	Max.	
V_{io}	Input Offset Voltage ($V_{ic} = V_o = V_{CC}/2$) $T_{min.} \leq T_{amb} \leq T_{max.}$	TS912 TS912A TS912B		10 5 2	mV
		TS912 TS912A TS912B		12 7 3	
DV_{io}	Input Offset Voltage Drift		5		$\mu V/^{\circ}C$
I_{io}	Input Offset Current - (note 1) $T_{min.} \leq T_{amb} \leq T_{max.}$		1	100 200	μA
I_{ib}	Input Bias Current - (note 1) $T_{min.} \leq T_{amb} \leq T_{max.}$		1	150 300	μA
I_{CC}	Supply Current (per amplifier, $A_{VCL} = 1$, no load) $T_{min.} \leq T_{amb} \leq T_{max.}$		400	600 700	μA
CMR	Common Mode Rejection Ratio $V_{ic} = 3$ to $7V$, $V_o = 5V$ $V_{ic} = 0$ to $10V$, $V_o = 5V$		60 50	90 75	dB
SVR	Supply Voltage Rejection Ratio ($V_{CC^+} = 5$ to $10V$, $V_o = V_{CC}/2$)		60	90	dB
A_{vd}	Large Signal Voltage Gain ($R_L = 10k\Omega$, $V_o = 2.5V$ to $7.5V$) $T_{min.} \leq T_{amb} \leq T_{max.}$		20 15	60	V/mV
V_{OH}	High Level Output Voltage ($V_{id} = 1V$) $T_{min.} \leq T_{amb} \leq T_{max.}$	$R_L = 100k\Omega$ $R_L = 10k\Omega$ $R_L = 600\Omega$ $R_L = 100\Omega$ $R_L = 10k\Omega$ $R_L = 600\Omega$	9.95 9.85 9 9.8 8.8	9.95 9.35 7.8	V
V_{OL}	Low Level Output Voltage ($V_{id} = -1V$) $T_{min.} \leq T_{amb} \leq T_{max.}$	$R_L = 100k\Omega$ $R_L = 10k\Omega$ $R_L = 600\Omega$ $R_L = 100\Omega$ $R_L = 10k\Omega$ $R_L = 600\Omega$		50 150 650 800 150 900	mV
I_o	Output Short Circuit Current ($V_{id} = \pm 1V$)	Source ($V_o = V_{CC^-}$) Sink ($V_o = V_{CC^+}$)	45 50	65 75	mA
GBP	Gain Bandwidth Product ($A_{VCL} = 100$, $R_L = 10k\Omega$, $C_L = 100pF$, $f = 100kHz$)			1.4	MHz
SR^+	Slew Rate ($A_{VCL} = 1$, $R_L = 10k\Omega$, $C_L = 100pF$, $V_i = 2.5V$ to $7.5V$)			1.3	V/ μs
SR^-	Slew Rate ($A_{VCL} = 1$, $R_L = 10k\Omega$, $C_L = 100pF$, $V_i = 2.5V$ to $7.5V$)			0.8	V/ μs
ϕ_m	Phase Margin			40	Degrees
e_n	Equivalent Input Noise Voltage ($R_s = 100\Omega$, $f = 1kHz$)			30	$\frac{nV}{\sqrt{Hz}}$
THD	Total Harmonic Distortion ($A_{VCL} = 1$, $R_L = 10k\Omega$, $C_L = 100pF$, $V_o = 4.75V$ to $5.25V$, $f = 1kHz$)			0.024	%
C_{in}	Input Capacitance			1.5	pF
V_{O1}/V_{O2}	Channel Separation ($f = 1kHz$)			120	dB

Note 1 : Maximum values including unavoidable inaccuracies of the industrial test.

TYPICAL CHARACTERISTICS

Figure 1 : Supply Current (each amplifier) versus Supply Voltage

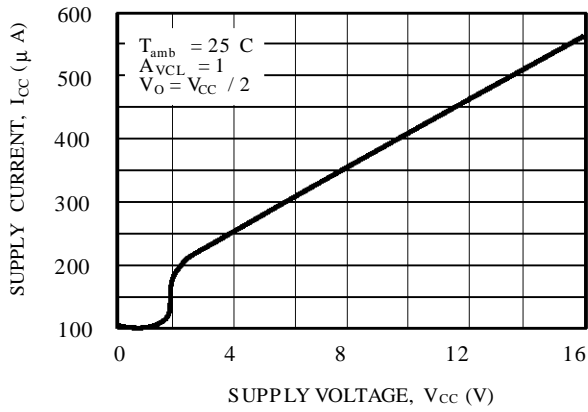


Figure 2 : Input Bias Current versus Temperature

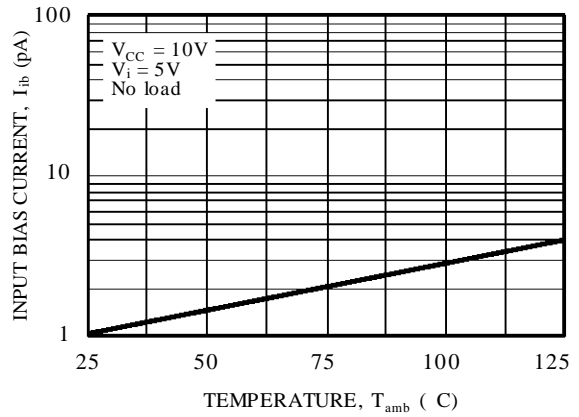


Figure 3a : High Level Output Voltage versus High Level Output Current

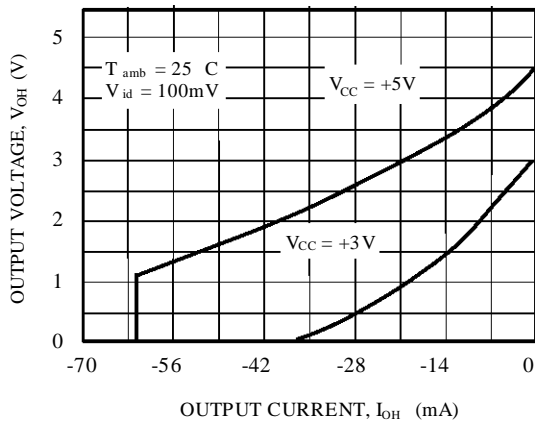


Figure 3b : High Level Output Voltage versus High Level Output Current

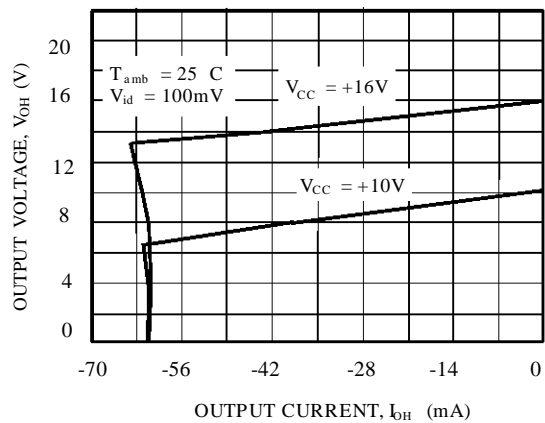


Figure 4a : Low Level Output Voltage versus Low Level Output Current

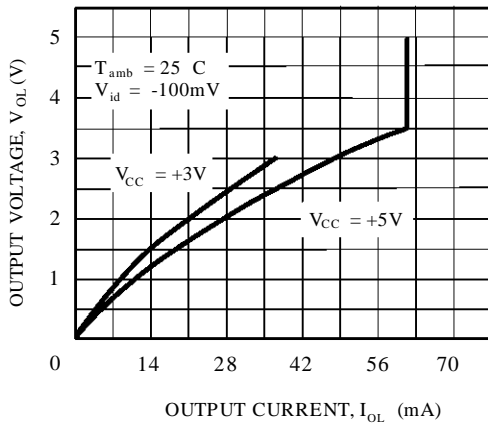


Figure 4b : Low Level Output Voltage versus Low Level Output Current

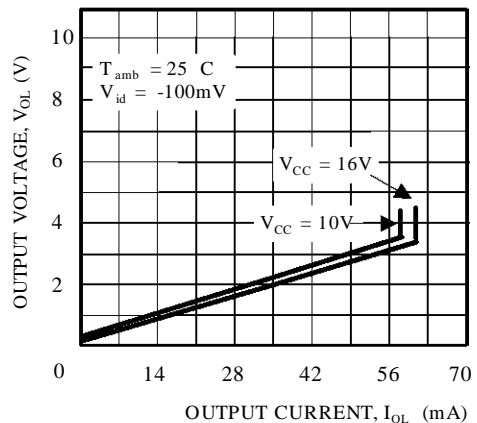


Figure 5a : Open Loop Frequency Response and Phase Shift

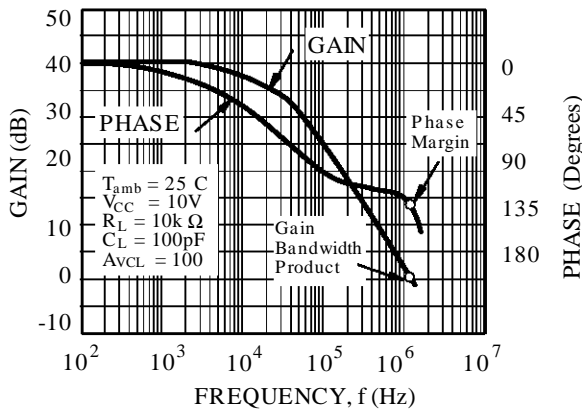


Figure 5b : Open Loop Frequency Response and Phase Shift

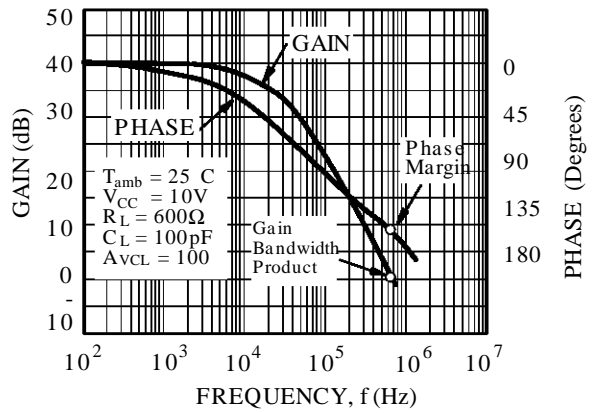


Figure 6a : Gain Bandwidth Product versus Supply Voltage

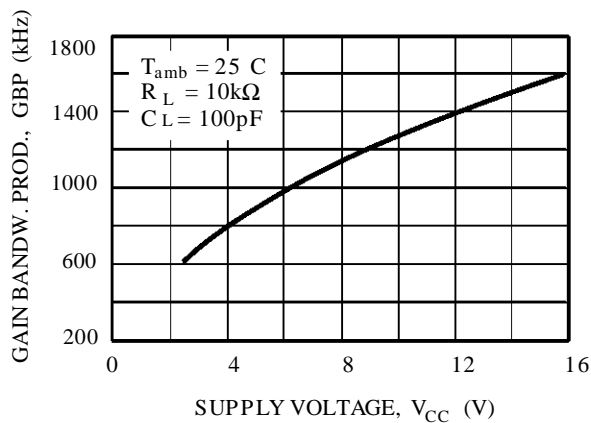


Figure 6b : Gain bandwidth Product versus Supply Voltage

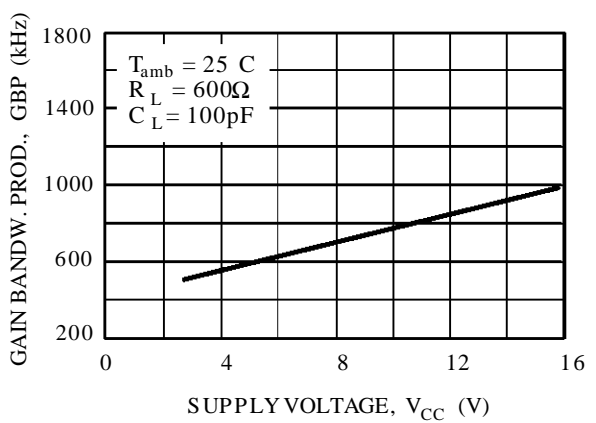


Figure 7a : Phase Margin versus Supply Voltage

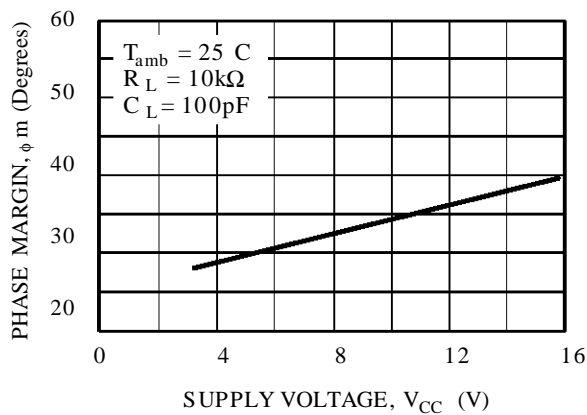


Figure 7b : Phase Margin versus Supply Voltage

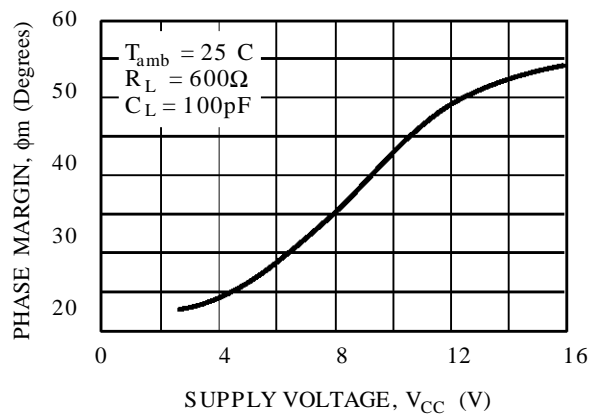
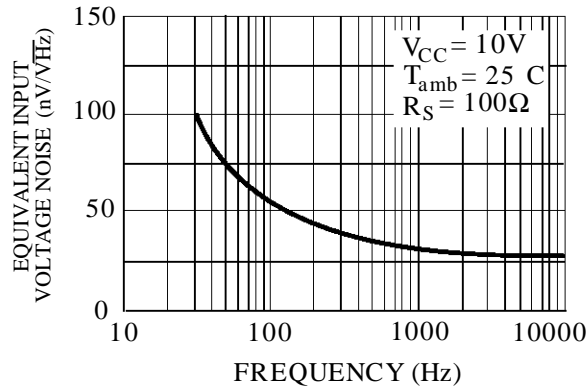
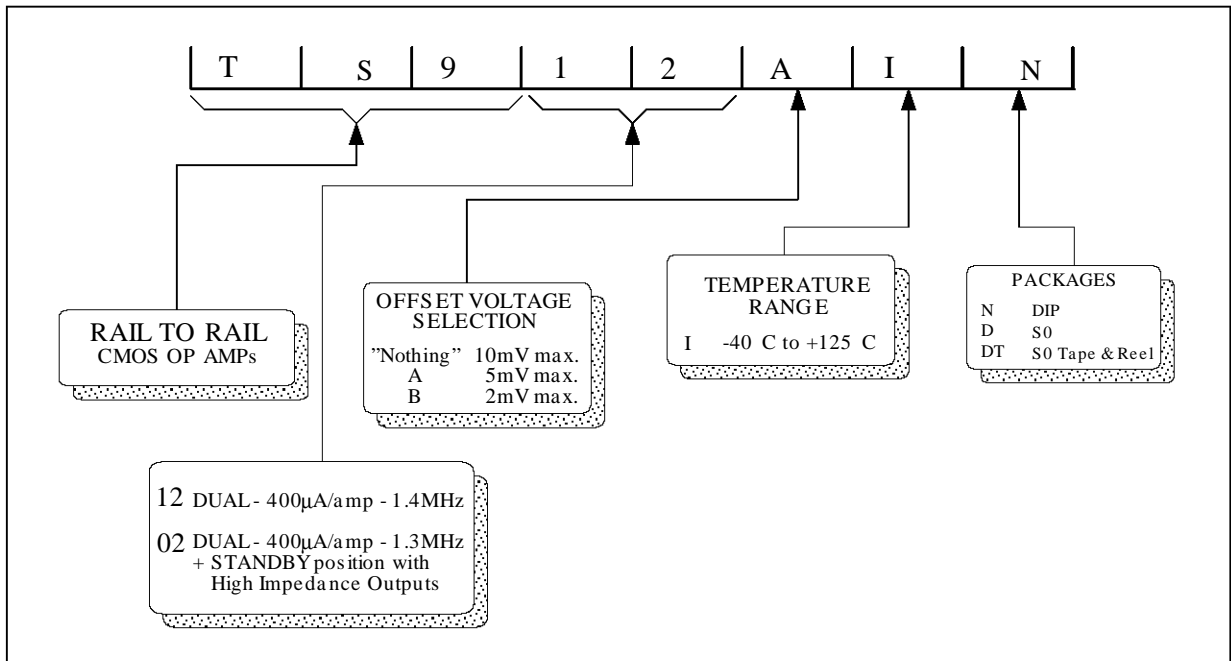


Figure 8 : Input Voltage Noise versus Frequency



ORDERING INFORMATION



MACROMODEL

- **RAIL TO RAIL** INPUT AND OUTPUT VOLTAGE RANGES
- SINGLE (OR DUAL) SUPPLY OPERATION FROM **2.7V TO 16V** ($\pm 1.35V$ to $\pm 8V$)
- EXTREMELY LOW INPUT BIAS CURRENT : **1pA typ.**
- LOW INPUT OFFSET VOLTAGE : **2mV max.**
- SPECIFIED FOR **600 Ω** AND **100 Ω** LOADS
- LOW SUPPLY CURRENT : 400 μ A/Ampli
- SPEED : 1.4MHz - 1.3V/ μ s

Applies to : TS912I,AI

** Standard Linear Ics Macromodels, 1993.

** CONNECTIONS :

* 1 INVERTING INPUT

* 2 NON-INVERTING INPUT

* 3 OUTPUT

* 4 POSITIVE POWER SUPPLY

* 5 NEGATIVE POWER SUPPLY

.SUBCKT TS912 1 3 2 4 5 (analog)

.MODEL MDTH D IS=1E-8 KF=6.563355E-14 CJO=10F

* INPUT STAGE

CIP 2 5 1.500000E-12

CIN 1 5 1.500000E-12

EIP 10 5 2 5 1

EIN 16 5 1 5 1

RIP 10 11 6.500000E+00

RIN 15 16 6.500000E+00

RIS 11 15 7.655100E+00

DIP 11 12 MDTH 400E-12

DIN 15 14 MDTH 400E-12

VOFP 12 13 DC 0.000000E+00

VOFN 13 14 DC 0

IPOL 13 5 4.000000E-05

CPS 11 15 3.82E-08

DINN 17 13 MDTH 400E-12

VIN 17 5 -0.5000000E+00

DINR 15 18 MDTH 400E-12

VIP 4 18 -0.5000000E+00

FCP 4 5 VOFP 7.750000E+00

FCN 5 4 VOFN 7.750000E+00

* AMPLIFYING STAGE

FIP 5 19 VOFP 5.500000E+02

FIN 5 19 VOFN 5.500000E+02

RG1 19 5 5.087344E+05

RG2 19 4 5.087344E+05

CC 19 29 2.200000E-08

HZTP 30 29 VOFP 12.33E+02

HZTN 5 30 VOFN 12.33E+02

DOPM 19 22 MDTH 400E-12

DONM 21 19 MDTH 400E-12

HOPM 22 28 VOUT 3135

VIPM 28 4 150

HONM 21 27 VOUT 3135

VINM 5 27 150

EOUT 26 23 19 5 1

VOUT 23 5 0

ROUT 26 3 65

COUT 3 5 1.000000E-12

DOP 19 68 MDTH 400E-12

VOP 4 25 1.924

HSCP 68 25 VSCP1 1E8

DON 69 19 MDTH 400E-12

VON 24 5 2.4419107

HSCN 24 69 VSCN1 1.5E8

VSCTHP 60 61 0.1375

DSCP1 61 63 MDTH 400E-12

VSCP1 63 64 0

ISCP 64 0 1.000000E-8

DSCP2 0 64 MDTH 400E-12

DSCN2 0 74 MDTH 400E-12

ISCN 74 0 1.000000E-8

VSCN1 73 74 0

DSCN1 71 73 MDTH 400E-12

VSCTHN 71 70 -0.75

ESCP 60 0 2 1 500

ESCN 70 0 2 1 -2000

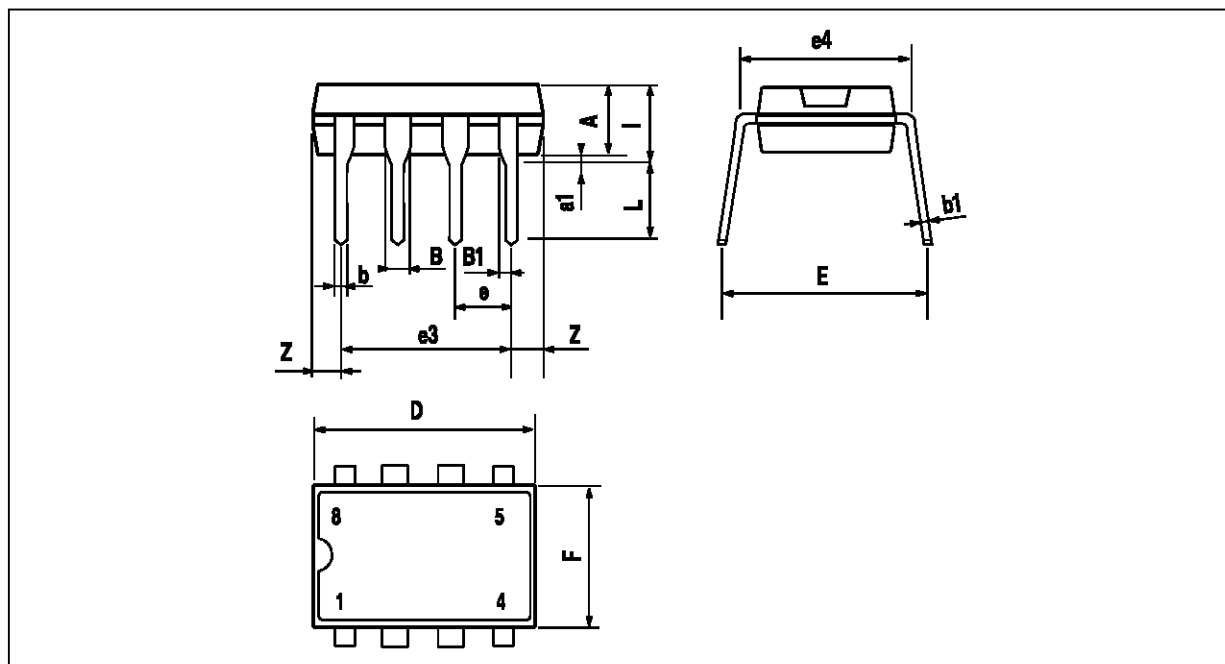
.ENDS

ELECTRICAL CHARACTERISTICS

$V_{CC}^+ = 10V$, $V_{CC}^- = 0V$, R_L, C_L connected to $V_{CC}/2$, $T_{amb} = 25^\circ C$
(unless otherwise specified)

Symbol	Conditions	Value	Unit
V_{io}		0	mV
A_{vd}	$R_L = 10k\Omega$	20	V/mV
I_{CC}	No load, per operator	350	μA
V_{icm}		-0.2 to 10.2	V
V_{OH}	$R_L = 10k\Omega$	9.95	V
V_{OL}	$R_L = 10k\Omega$	50	mV
I_{sink}	$V_O = 10V$	50	mA
I_{source}	$V_O = 0V$	50	mA
GBP	$R_L = 10k\Omega$, $C_L = 100pF$	1	MHz
SR	$R_L = 10k\Omega$, $C_L = 100pF$	1	V/ μs
$\varnothing m$	$R_L = 10k\Omega$, $C_L = 100pF$	40	Degrees

PACKAGE MECHANICAL DATA
8 PINS - PLASTIC DIP

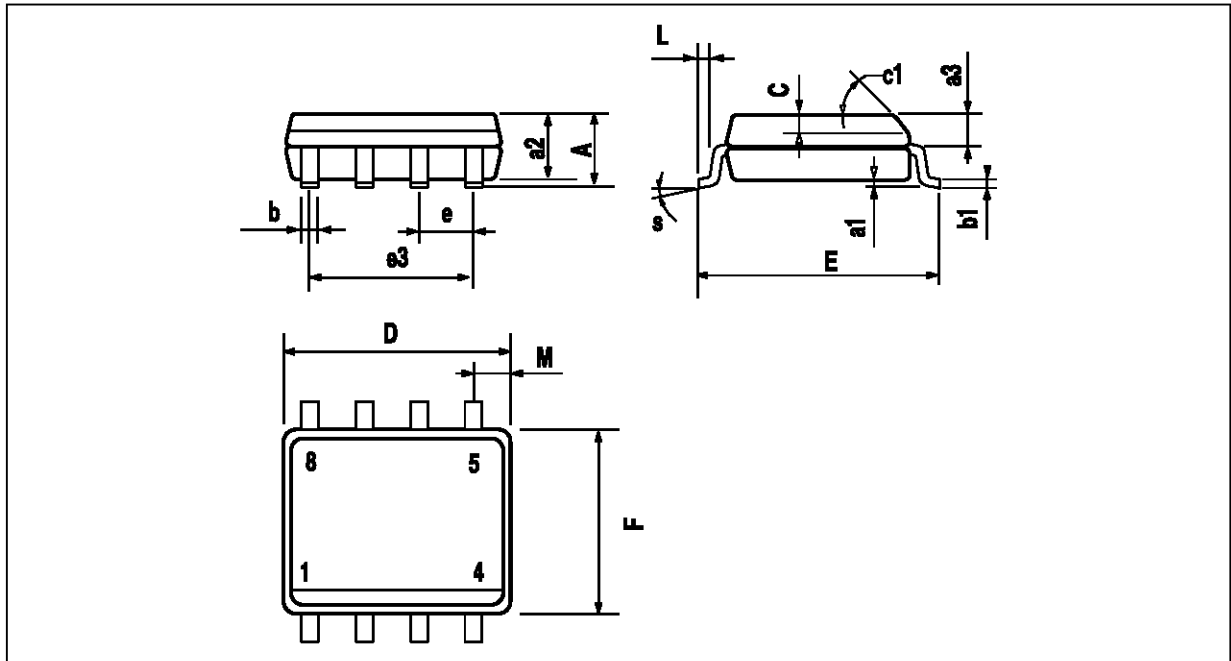


PM-DIP8.EPS

Dimensions	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A		3.32			0.131	
a1	0.51			0.020		
B	1.15		1.65	0.045		0.065
b	0.356		0.55	0.014		0.022
b1	0.204		0.304	0.008		0.012
D			10.92			0.430
E	7.95		9.75	0.313		0.384
e		2.54			0.100	
e3		7.62			0.300	
e4		7.62			0.300	
F			6.6			0.260
i			5.08			0.200
L	3.18		3.81	0.125		0.150
Z			1.52			0.060

DIP8.TBL

PACKAGE MECHANICAL DATA
 8 PINS - PLASTIC MICROPACKAGE (SO)



PM-S08:EPS

Dimensions	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A			1.75			0.069
a1	0.1		0.25	0.004		0.010
a2			1.65			0.065
a3	0.65		0.85	0.026		0.033
b	0.35		0.48	0.014		0.019
b1	0.19		0.25	0.007		0.010
C	0.25		0.5	0.010		0.020
c1	45° (typ.)					
D	4.8		5.0	0.189		0.197
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		3.81			0.150	
F	3.8		4.0	0.150		0.157
L	0.4		1.27	0.016		0.050
M			0.6			0.024
S	8° (max.)					

S08.TEL

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